

**Amendments to the Specification:**

Please replace the paragraph beginning on line 16 of page 10 with the following amended paragraph:

Fig. 8 illustrates another alternate embodiment atomic layer deposition apparatus 10d. Like numerals from the above-described embodiments are utilized where appropriate, with differences being indicated with the suffix "d", or with different numerals. Atomic layer deposition apparatus 10d comprises a third non-roughing vacuum pump 60 60d in fluid communication with chamber 12d apart from substrate passageway 14. In one preferred embodiment, third non-roughing vacuum pump 60d is configured with chamber 12d for feeding a second deposition precursor to chamber 12d. For example, in one preferred embodiment, separate precursor feed pumps (i.e., pumps 26d and 60d) are separately optimized for their respective different deposition precursors (for example, in one or both of materials of construction or designed throughput) while another of the non-roughing vacuum pumps (i.e., pump 28d) is configured for feeding a purge gas to the chamber (for example, with respect to desired higher throughput than with the deposition precursors).